New Jersey Semi-Conductor Products, Inc.

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2N4302

N–Channel JFET Silicon Transistor
General Purpose AF Amplifier

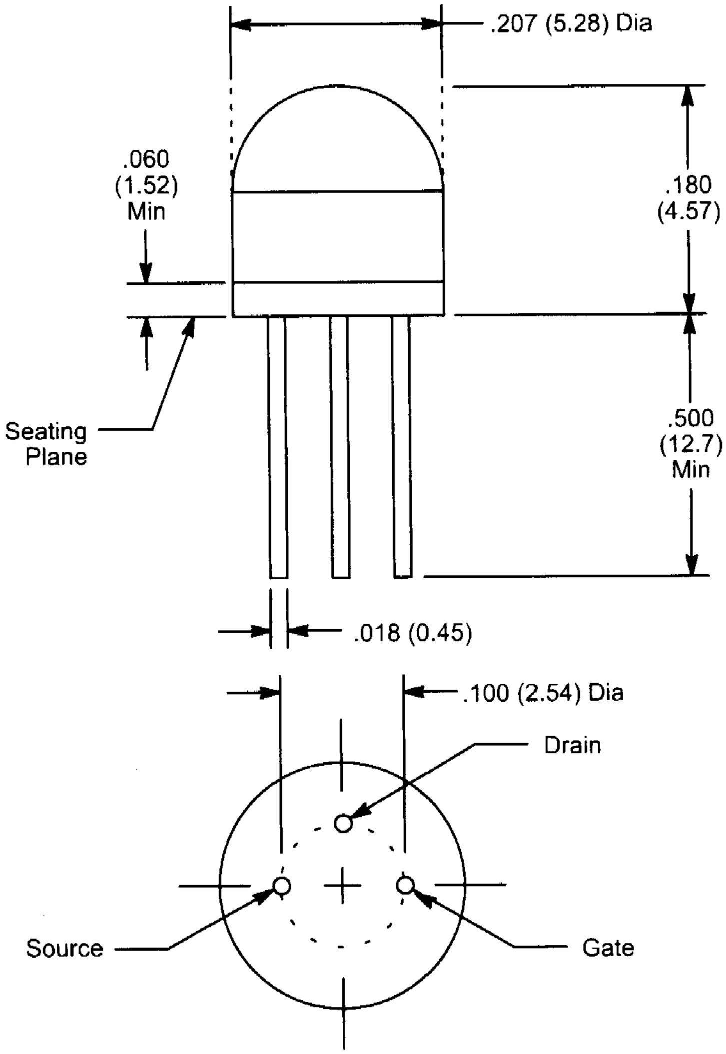
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Drain–Source Voltage, V_{DS}	25V
Drain–Gate Voltage, V_{DG}	25V
Gate–Source Voltage, V_{GS}	–25V
Gate Current, I_G	10mA
Total Device Dissipation (T_A = +25°C), P_D	300mW
Derate Above 25°C	2mW/°C
Operating Junction Temperature Range, T_J	–55° to +150°C
Storage Temperature Range, T_{stg}	–55° to +150°C
Lead Temperature (During Soldering, 1/16" from case for 10sec), T_L	+260°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate–Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = 1\mu A$, $V_{DS} = 0$	–25	–	–	V
Gate Reverse Current	I_{GSS}	$V_{GS} = 20V$, $V_{DS} = 0$	–	–	–1	nA
		$V_{GS} = 20V$, $V_{DS} = 0$, $T_A = +150°C$	–	–	–1	µA
Gate–Source Cutoff Voltage	$V_{GS(off)}$	$I_D = 1\mu A$, $V_{DS} = 15V$	–	–	-6.5	V
Gate–Source Voltage	V_{GS}	$I_D = 50\mu A$, $V_{DS} = 15V$	–0.4	–	–6.0	V
Zero–Gate–Voltage Drain Current	I_{DSS}	$V_{DS} = 15V$, $V_{GS} = 0$	0.5	–	15	mA
Forward Transfer Admittance	$\|y_{fs}\|$	$V_{DS} = 15V$, $V_{GS} = 0$, f = 1kHz	1000	–	7500	µmho

Quality Semi-Conductors


.207 (5.28) Dia
.060
(1.52)
Min
.180
(4.57)
Seating
Plane
.500
(12.7)
Min
.018 (0.45)
.100 (2.54) Dia
Drain
Source
Gate